

# 模拟电路知识点小结

最新版: <https://github.com/chenshuo/nuedc>

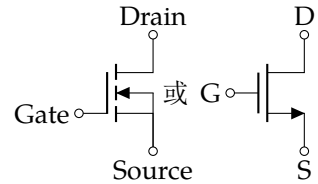
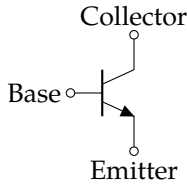
## Transistor

器件

BJT (NPN)

MOSFET (n-channel, enh.)

符号

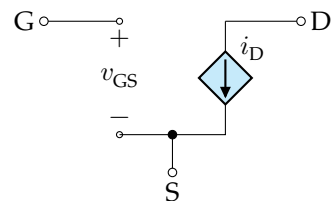
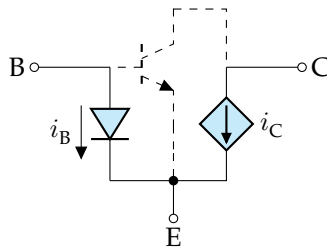


大信号模型

Ebers-Moll

Shichman-Hodges

BJT 放大区  
MOS 管恒流区



$$i_C = I_S \exp \frac{v_{BE}}{V_T}$$

$$i_B = \frac{i_C}{\beta}$$

$$i_E = i_B + i_C = (1 + \beta) i_B$$

$$0 < v_{GS} - V_{th} \leq v_{DS} :$$

$$i_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (v_{GS} - V_{th})^2$$

$$0 < v_{DS} < v_{GS} - V_{th} :$$

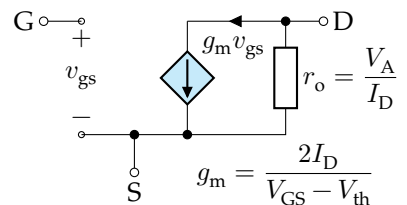
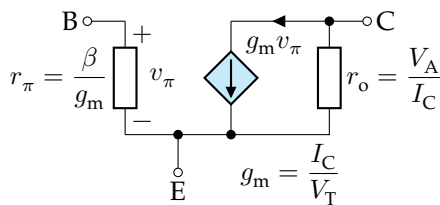
$$i_D = \mu_n C_{ox} \frac{W}{L} [(v_{GS} - V_{th}) v_{DS} - \frac{v_{DS}^2}{2}]$$

$$i_D = i_{D0} \left( 1 + \frac{v_{DS}}{V_A} \right) = i_{D0} (1 + \lambda v_{DS})$$

Early 效应

$$i_C = i_{C0} \left( 1 + \frac{v_{CE}}{V_A} \right)$$

低频小信号模型  
hybrid-pi



跨导  $g_m$

$$g_m = \frac{I_C}{V_T}$$

$$g_m = \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{th})$$

$$= \sqrt{2 \mu_n C_{ox} \frac{W}{L} I_D}$$

输入阻抗  $r_{be}, r_\pi$

$$r_\pi = \frac{V_T}{I_B} \approx \frac{\beta}{g_m}$$

输出阻抗  $r_{ce}, r_o$

$$r_o = \frac{V_A + V_{CE}}{I_C} \approx \frac{V_A}{I_C}$$

本征增益  $A_0 \equiv g_m r_o$

$$A_0 = \frac{V_A}{V_T}$$

$$r_i = \infty$$

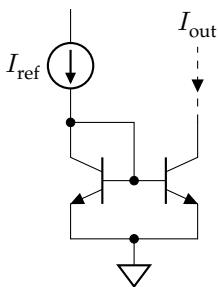
$$r_o = \frac{V_A}{I_D} = \frac{1}{\lambda I_D}$$

$$A_0 = \frac{2V_A}{V_{GS} - V_{th}}$$

# BJT 电流源

类型

Mirror



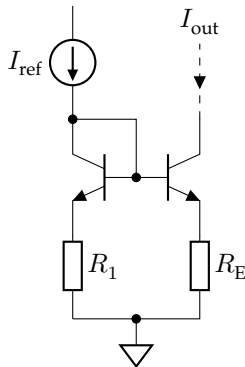
输出电流  $I_{out}$

$$I_{out} = \frac{I_{ref}}{1 + 2/\beta} \approx I_{ref}$$

输出阻抗  $R_o$

$$R_o = r_o \approx \frac{V_A}{I_C}$$

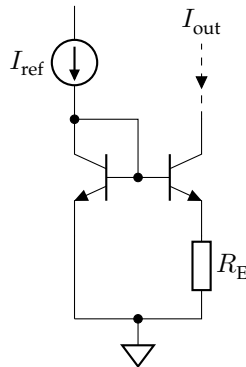
Emitter degeneration



$$I_{out} \approx \frac{R_1}{R_E} I_{ref}$$

$$R_o \approx r_o [1 + g_m (R_E // r_{\pi})]$$

Widlar 微电流源



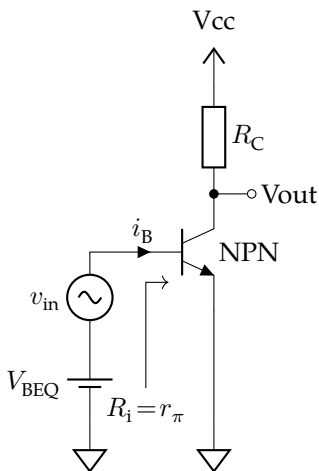
$$I_{out} R_E = V_T \ln \frac{I_{ref}}{I_{out}}$$

$$\text{同左, 但通常 } R_E \ll r_{\pi}$$

## 单管 Common-Emitter 放大电路

Type

Basic



输入阻抗  $R_i$

$$R_i = r_{\pi} = \frac{V_T}{I_B} \approx \frac{\beta}{g_m}$$

输出阻抗  $R_o$

$$R_o = R_C // r_o \approx R_C$$

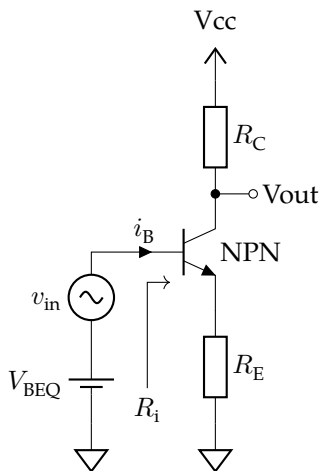
空载增益  $A_{v0}$

$$g_m (R_C // r_o) \approx g_m R_C$$

max  $A_{v0}$

$$A_{v0} = \frac{I_C R_C}{V_T} < \frac{V_{CC}}{V_T}$$

Emitter degeneration

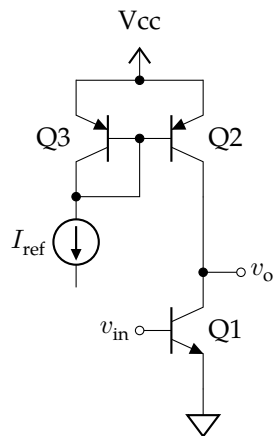


$$R_i = r_{\pi} + (1 + \beta) R_E$$

$$R_o \approx R_C$$

$$\frac{R_C}{1/g_m + R_E} \approx \frac{R_C}{R_E}$$

Active load



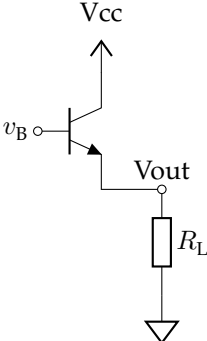
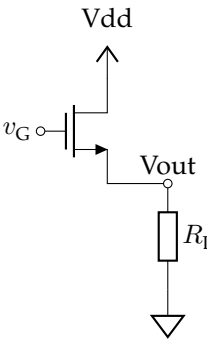
$$R_i = r_{\pi}$$

$$R_o = r_{o1} // r_{o2}$$

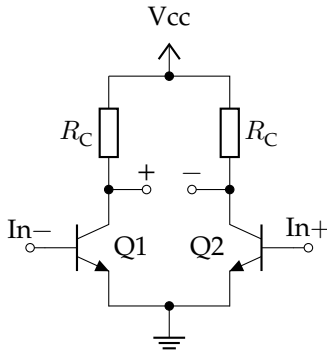
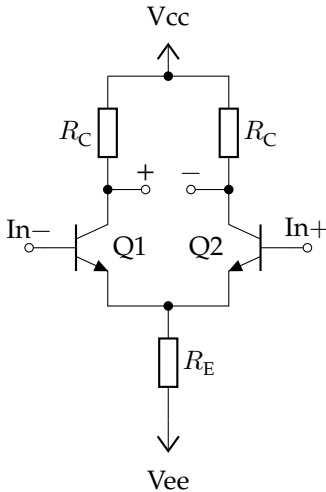
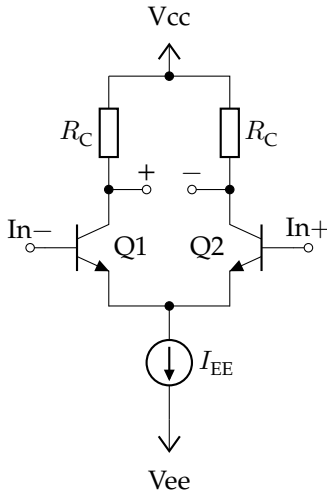
$$g_m (r_{o1} // r_{o2})$$

$$A_{v0} = \frac{V_{A1} V_{A2}}{V_T (V_{A1} + V_{A2})}$$

电压跟随器

类型	NPN 射极跟随器	NMOS 源极跟随器
电路		
输入阻抗 $R_i$	$r_\pi + (1 + \beta)R_L$	$\infty$
输出阻抗 $R_o$	$R_o = \frac{\alpha}{g_m} \approx \frac{1}{g_m}$	$R_o \approx \frac{1}{g_m}$
增益 $A_v$	$\frac{R_L}{R_L + \alpha/g_m}$	$\frac{R_L}{R_L + 1/g_m}$

Differential-Pair

电路	Basic	Long tail	电流源偏置
			

# 有源负载 / 五管 OTA (operational transconductance amplifier )

